

Abstract of the Disclosure

The present invention provides a semiconductor memory device capable of preventing bridge formations in a peripheral circuit region and improving a process margin and a method for fabricating the same. The semiconductor memory device includes: a cell region; a peripheral circuit region adjacent to the cell region; and a plurality of line patterns formed in the cell region and the peripheral circuit region, wherein a spacing distance between the line patterns is at least onefold greater than a width of the line pattern.